

Substitute for form 14498/PTO

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Application Number	09/160,657
Filing Date	September 25, 1998
First Named Inventor	Joseph W. Lyding
Art Unit	2822
Examiner Name	VOCKRODT, Jeff B.
Attorney Docket Number	UIL-10013C

Examiner Initials*	Cite No.	Include Name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published
JV		A. UCHIYAMA, H. FUKUDA, T. HAYASHI, T. IWABUCHI, S. OHNO "High Performance Dual-gate Sub-halfmicron CMOSFETs with 6nm-thick Nitrided SiO ₂ Films in an N ₂ O Ambient", IEDM Tech. Dig. 1990, pp 16.6.1 – 16.6.4
Examiner Signature		Date Considered
[Signature]		5-2-03

Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if the English language Translation is attached.
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